

PLUS Search Results for S/N 10689792, Searched February 21, 2006

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Titles of Most Frequently Occurring Classifications of Patents Returned  
From A Search of 10689792 on February 21, 2006

5 438/624 (2 OR, 3 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL

438/597 .To form ohmic contact to semiconductive  
material

438/618 ..Contacting multiple semiconductive regions  
(i.e., interconnects)

438/622 ...Multiple metal levels, separated by  
insulating layer (i.e., multiple level metallization)

438/624 ....Separating insulating layer is laminate or  
composite of plural insulating materials

4 428/433 (0 OR, 4 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES

428/411.1 COMPOSITE (NONSTRUCTURAL LAMINATE)

428/426 .Of quartz or glass

428/432 ..Next to metal or compound thereof

428/433 ...Alloy or free metal

4 428/461 (1 OR, 3 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES

428/411.1 COMPOSITE (NONSTRUCTURAL LAMINATE)

428/457 .Of metal

428/461 ..Next to addition polymer from unsaturated  
monomers

4 438/637 (0 OR, 4 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL

438/597 .To form ohmic contact to semiconductive  
material

438/618 ..Contacting multiple semiconductive regions  
(i.e., interconnects)

438/622 ...Multiple metal levels, separated by  
insulating layer (i.e., multiple level metallization)

438/637 ....With formation of opening (i.e., viahole)  
in insulative layer

3 257/758 (1 OR, 2 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES

257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD

257/741 .Of specified material other than unalloyed  
aluminum

257/750 ..Layered

257/758 ...Multiple metal levels on semiconductor,  
separated by insulating layer (e.g., multiple level  
metallization for integrated circuit)

3 257/E21.162 (0 OR, 3 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE  
OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE  
DEVICES OR OF

PARTS THEREOF (EPO)

257/E21.002 .Manufacture or treatment of semiconductor

257/E21.04 ..Device having at least one potential-jump  
 depletion barrier or surface barrier, e.g., PN junction,  
 layer, carrier concentration layer (EPO)  
 257/E21.085 ...Device having semiconductor body comprising  
 without Group IV elements or Group III-V compounds with or  
 impurities, e.g., doping materials (EPO)  
 257/E21.158 ....Manufacture of electrode on semiconductor  
 materials, or body using process other than by epitaxial growth,  
 diffusion of impurities, alloying of impurity  
 257/E21.159 .....radiation bombardment (EPO)  
 (EPO) .....Deposition of conductive or insulating  
 material for electrode conducting electric current  
 257/E21.16 .....From a gas or vapor, e.g., condensation  
 (EPO)  
 257/E21.161 .....Of conductive layer (EPO)  
 257/E21.162 .....On semiconductor body comprising Group  
 IV element (EPO)

3 257/E21.245 (0 OR, 3 XR)  
 Class 257 : ACTIVE SOLID-STATE DEVICES  
 257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE  
 OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE  
 DEVICES OR OF  
 PARTS THEREOF (EPO)  
 257/E21.002 .Manufacture or treatment of semiconductor  
 device (EPO)  
 257/E21.04 ..Device having at least one potential-jump  
 depletion barrier or surface barrier, e.g., PN junction,  
 layer, carrier concentration layer (EPO)  
 257/E21.085 ...Device having semiconductor body comprising  
 without Group IV elements or Group III-V compounds with or  
 impurities, e.g., doping materials (EPO)  
 257/E21.211 ....Treatment of semiconductor body using  
 material on process other than deposition of semiconductor  
 material, or a substrate, diffusion or alloying of impurity  
 257/E21.214 .....radiation treatment (EPO)  
 cutting .....To change their surface-physical  
 characteristics or shape, e.g., etching, polishing,  
 (EPO)  
 257/E21.24 .....To form insulating layer thereon, e.g.,  
 (EPO) for masking or by using photolithographic technique  
 257/E21.241 .....Post-treatment (EPO)  
 257/E21.243 .....Planarization of insulating layer (EPO)  
 257/E21.244 .....Involving dielectric removal step  
 (EPO)  
 257/E21.245 .....Removal by chemical etching, e.g.,  
 dry etching (EPO)

3 257/E21.266 (0 OR, 3 XR)  
 Class 257 : ACTIVE SOLID-STATE DEVICES  
 Page 2

257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE  
OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE  
DEVICES OR OF PARTS THEREOF (EPO)

257/E21.002 .Manufacture or treatment of semiconductor  
device (EPO)

257/E21.04 ..Device having at least one potential-jump  
barrier or surface barrier, e.g., PN junction,  
depletion layer, carrier concentration layer (EPO)

257/E21.085 ...Device having semiconductor body comprising  
Group IV elements or Group III-V compounds with or  
without impurities, e.g., doping materials (EPO)

257/E21.211 ....Treatment of semiconductor body using  
process other than deposition of semiconductor  
material on a substrate, diffusion or alloying of impurity  
material, or radiation treatment (EPO)

257/E21.214 .....To change their surface-physical  
characteristics or shape, e.g., etching, polishing,  
cutting (EPO)

257/E21.24 .....To form insulating layer thereon, e.g.,  
for masking or by using photolithographic technique  
(EPO)

257/E21.266 .....Inorganic layer (EPO)

3 257/E21.295 (0 OR, 3 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE  
OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE  
DEVICES OR OF PARTS THEREOF (EPO)

257/E21.002 .Manufacture or treatment of semiconductor  
device (EPO)

257/E21.04 ..Device having at least one potential-jump  
barrier or surface barrier, e.g., PN junction,  
depletion layer, carrier concentration layer (EPO)

257/E21.085 ...Device having semiconductor body comprising  
Group IV elements or Group III-V compounds with or  
without impurities, e.g., doping materials (EPO)

257/E21.211 ....Treatment of semiconductor body using  
process other than deposition of semiconductor  
material on a substrate, diffusion or alloying of impurity  
material, or radiation treatment (EPO)

257/E21.214 .....To change their surface-physical  
characteristics or shape, e.g., etching, polishing,  
cutting (EPO)

257/E21.294 .....Deposition/post-treatment of  
noninsulating, e.g., conductive - or resistive - layers  
on insulating layers (EPO)

257/E21.295 .....Deposition of layer comprising metal,  
e.g., metal, alloys, metal compounds (EPO)

- 3 257/E21.58 (0 OR, 3 XR)  
 Class 257 : ACTIVE SOLID-STATE DEVICES  
 257/E21.531 ...For electrical parameters, e.g.,  
 resistance, deep-levels, CV, diffusions by  
 electrical means  
 (EPO)  
 257/E21.532 .Manufacture or treatment of devices  
 consisting of plurality of solid-state components  
 formed in  
 or on common substrate or of parts thereof;  
 manufacture of  
 integrated circuit devices or of parts thereof (EPO)  
 257/E21.536 ..Manufacture of specific parts of devices  
 (EPO)  
 257/E21.575 ...Interconnections, comprising conductors and  
 dielectrics, for carrying current between separate  
 components within device (EPO)  
 257/E21.576 ....Characterized by formation and post  
 treatment of dielectrics, e.g., planarizing (EPO)  
 257/E21.58 .....Planarizing dielectric (EPO)
- 3 257/E23.145 (0 OR, 3 XR)  
 Class 257 : ACTIVE SOLID-STATE DEVICES  
 257/E23.139 ...Liquid at normal operating temperature of  
 device (EPO)  
 257/E23.141 .Arrangements for conducting electric current  
 within device in operation from one component to  
 another,  
 interconnections, e.g., wires, lead frames (EPO)  
 257/E23.142 ..Including external interconnections  
 consisting of multilayer structure of conductive and  
 insulating layers inseparably formed on semiconductor  
 body  
 (EPO)  
 257/E23.145 ...Via connections in multilevel  
 interconnection structure (EPO)
- 3 428/209 (0 OR, 3 XR)  
 Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
 428/98 STRUCTURALLY DEFINED WEB OR SHEET (E.G.,  
 OVERALL DIMENSION, ETC.)  
 428/195.1 .Discontinuous or differential coating,  
 impregnation or bond (e.g., artwork, printing, retouched  
 photograph, etc.)  
 428/209 ..Including metal layer
- 3 428/35.9 (1 OR, 2 XR)  
 Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
 428/34.1 HOLLOW OR CONTAINER TYPE ARTICLE (E.G., TUBE,  
 VASE, ETC.)  
 428/35.7 .Polymer or resin containing (i.e., natural or  
 synthetic)  
 428/35.8 ..Elemental metal containing (e.g., substrate,  
 foil, film, coating, etc.)  
 428/35.9 ...Three or more layers (continuous layer)
- 2 117/108 (0 OR, 2 XR)  
 Class 117 : SINGLE-CRYSTAL, ORIENTED-CRYSTAL, AND EPITAXY  
 GROWTH PROCESSES; NON-COATING APPARATUS THEREFOR  
 117/84 FORMING FROM VAPOR OR GASEOUS STATE (E.G., VPE,  
 SUBLIMATION)  
 117/108 .Using an energy beam or field, a particle beam  
 or field, or a plasma (e.g., MBE)

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- 2 117/940 (0 OR, 2 XR)  
 Class 117 : SINGLE-CRYSTAL, ORIENTED-CRYSTAL, AND EPITAXY  
 GROWTH PROCESSES; NON-COATING APPARATUS THEREFOR  
 117/937 INORGANIC CONTAINING SINGLE-CRYSTAL (E.G.,  
 COMPOUND, MIXTURE, COMPOSITE) {C30B 29/10}  
 117/940 .Halide containing (e.g., fluorphlogopite,  
 fluor-mica) {C30B 29/12}
- 2 118/308 (0 OR, 2 XR)  
 Class 118 : COATING APPARATUS  
 118/300 PROJECTION OR SPRAY TYPE  
 118/308 .Applying solid particulate material
- 2 118/323 (0 OR, 2 XR)  
 Class 118 : COATING APPARATUS  
 118/300 PROJECTION OR SPRAY TYPE  
 118/323 .Moving projector
- 2 118/59 (1 OR, 1 XR)  
 Class 118 : COATING APPARATUS  
 118/58 WITH HEAT EXCHANGE, DRYING, OR NON-COATING GAS  
 OR VAPOR TREATMENT OF WORK  
 118/59 .with solid heat exchange means contacting work
- 2 118/673 (0 OR, 2 XR)  
 Class 118 : COATING APPARATUS  
 118/663 CONTROL MEANS RESPONSIVE TO A RANDOMLY  
 OCCURRING SENSED CONDITION  
 118/668 .Responsive to attribute, absence or presence  
 of work  
 118/672 ..Running length work  
 118/673 ...Edge of running length of web material  
 sensed
- 2 118/69 (0 OR, 2 XR)  
 Class 118 : COATING APPARATUS  
 118/58 WITH HEAT EXCHANGE, DRYING, OR NON-COATING GAS  
 OR VAPOR TREATMENT OF WORK  
 118/69 .Cooling
- 2 148/33.4 (1 OR, 1 XR)  
 Class 148 : METAL TREATMENT  
 148/33 BARRIER LAYER STOCK MATERIAL, P-N TYPE  
 148/33.4 .With contiguous layers of different  
 semiconductive material
- 2 148/33.5 (0 OR, 2 XR)  
 Class 148 : METAL TREATMENT  
 148/33 BARRIER LAYER STOCK MATERIAL, P-N TYPE  
 148/33.5 .Having at least three contiguous layers of  
 semiconductive material
- 2 216/13 (1 OR, 1 XR)  
 Class 216 : ETCHING A SUBSTRATE: PROCESSES  
 216/13 FORMING OR TREATING ELECTRICAL CONDUCTOR  
 ARTICLE (E.G., CIRCUIT, ETC.)
- 2 220/62.12 (2 OR, 0 XR)  
 Class 220 : RECEPTACLES  
 220/62.11 RECEPTACLE SIDE WALL MADE OF TWO OR MORE LAYERS  
 OF MATERIAL PERMANENTLY ATTACHED TOGETHER

220/62.12 .Beverage receptacle

- 2 220/669 (0 OR, 2 XR)  
 Class 220 : RECEPTACLES  
 220/660 SIDEWALL STRUCTURE  
 220/669 .Contoured sidewall (e.g., curved, corrugated,  
 ribbed, variable thickness, etc.)
- 2 228/121 (1 OR, 1 XR)  
 Class 228 : METAL FUSION BONDING  
 228/101 PROCESS  
 228/121 .Bonding nonmetals with metallic filler
- 2 228/122.1 (0 OR, 2 XR)  
 Class 228 : METAL FUSION BONDING  
 228/101 PROCESS  
 228/122.1 .Metal to nonmetal with separate metallic  
 filler
- 2 228/124.1 (0 OR, 2 XR)  
 Class 228 : METAL FUSION BONDING  
 228/101 PROCESS  
 228/122.1 .Metal to nonmetal with separate metallic  
 filler  
 228/124.1 ..With treating
- 2 228/195 (1 OR, 1 XR)  
 Class 228 : METAL FUSION BONDING  
 228/101 PROCESS  
 228/193 .Diffusion type  
 228/195 ..With incipient melting of bonding surface
- 2 257/750 (0 OR, 2 XR)  
 Class 257 : ACTIVE SOLID-STATE DEVICES  
 257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD  
 257/741 .Of specified material other than unalloyed  
 aluminum  
 257/750 ..Layered
- 2 257/751 (0 OR, 2 XR)  
 Class 257 : ACTIVE SOLID-STATE DEVICES  
 257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD  
 257/741 .Of specified material other than unalloyed  
 aluminum  
 257/750 ..Layered  
 257/751 ...At least one layer forms a diffusion barrier
- 2 257/761 (0 OR, 2 XR)  
 Class 257 : ACTIVE SOLID-STATE DEVICES  
 257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD  
 257/741 .Of specified material other than unalloyed  
 aluminum  
 257/750 ..Layered  
 257/761 ...At least one layer containing vanadium,  
 hafnium, niobium, zirconium, or tantalum
- 2 257/769 (0 OR, 2 XR)  
 Class 257 : ACTIVE SOLID-STATE DEVICES  
 257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD  
 257/741 .Of specified material other than unalloyed  
 aluminum  
 257/768 ..Refractory or platinum group metal or alloy

or silicide thereof

257/769 ...Platinum group metal or silicide thereof

2 257/E21.585 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.531 ...For electrical parameters, e.g.,  
resistance, deep-levels, CV, diffusions by

electrical means

(EPO)

257/E21.532 .Manufacture or treatment of devices  
consisting of plurality of solid-state components

formed in

or on common substrate or of parts thereof;

manufacture of

integrated circuit devices or of parts thereof (EPO)

257/E21.536 ..Manufacture of specific parts of devices  
(EPO)257/E21.575 ...Interconnections, comprising conductors and  
dielectrics, for carrying current between separate  
components within device (EPO)257/E21.576 ....Characterized by formation and post  
treatment of dielectrics, e.g., planarizing (EPO)257/E21.585 .....Filling of holes, grooves, vias or  
trenches with conductive material (EPO)

2 257/E21.59 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.531 ...For electrical parameters, e.g.,  
resistance, deep-levels, CV, diffusions by

electrical means

(EPO)

257/E21.532 .Manufacture or treatment of devices  
consisting of plurality of solid-state components

formed in

or on common substrate or of parts thereof;

manufacture of

integrated circuit devices or of parts thereof (EPO)

257/E21.536 ..Manufacture of specific parts of devices  
(EPO)257/E21.575 ...Interconnections, comprising conductors and  
dielectrics, for carrying current between separate  
components within device (EPO)257/E21.576 ....Characterized by formation and post  
treatment of dielectrics, e.g., planarizing (EPO)

257/E21.59 .....Local interconnects; local pads (EPO)

2 257/E23.106 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E23.079 ..For integrated circuit devices, e.g., power  
bus, number of leads (EPO)257/E23.08 .Arrangements for cooling, heating, ventilating  
or temperature compensation; temperature-sensing  
arrangements (EPO)257/E23.101 ..Selection of materials, or shaping, to  
facilitate cooling or heating, e.g., heat sinks (EPO)257/E23.106 ...Laminates or multilayers, e.g., direct bond  
copper ceramic substrates (EPO)

2 257/E23.147 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E23.139 ...Liquid at normal operating temperature of  
device (EPO)

257/E23.141 .Arrangements for conducting electric current



- another,  
 257/E23.142 ..Including external interconnections  
 consisting of multilayer structure of conductive and  
 insulating layers inseparably formed on semiconductor  
 body  
 (EPO)  
 257/E23.146 ...With adaptable interconnections (EPO)  
 257/E23.147 ....Comprising antifuses, i.e., connections  
 having their state changed from nonconductive to  
 conductive  
 (EPO)
- 2 257/E23.167 (0 OR, 2 XR)  
 Class 257 : ACTIVE SOLID-STATE DEVICES  
 257/E23.139 ...Liquid at normal operating temperature of  
 device (EPO)  
 257/E23.141 .Arrangements for conducting electric current  
 within device in operation from one component to  
 another,  
 257/E23.142 ..Including external interconnections  
 consisting of multilayer structure of conductive and  
 insulating layers inseparably formed on semiconductor  
 body  
 (EPO)  
 257/E23.154 ...Characterized by materials (EPO)  
 257/E23.167 ....Insulating materials (EPO)
- 2 257/E29.162 (0 OR, 2 XR)  
 Class 257 : ACTIVE SOLID-STATE DEVICES  
 257/E29.104 ....Si compounds (e.g., SiC) (EPO)  
 257/E29.111 .Electrodes (EPO)  
 257/E29.139 ..Of specified material (EPO)  
 257/E29.15 ...Electrodes for IGFET (EPO)  
 257/E29.162 ....Insulating materials for IGFET (EPO)
- 2 359/586 (0 OR, 2 XR)  
 Class 359 : OPTICS: SYSTEMS  
 359/577 LIGHT INTERFERENCE  
 359/580 .Produced by coating or lamina  
 359/586 ..Layers having specified index of refraction
- 2 427/422 (0 OR, 2 XR)  
 Class 427 : COATING PROCESSES  
 427/421.1 SPRAYING  
 427/422 .Heated coating material
- 2 427/424 (0 OR, 2 XR)  
 Class 427 : COATING PROCESSES  
 427/421.1 SPRAYING  
 427/424 .Moving the base
- 2 427/446 (1 OR, 1 XR)  
 Class 427 : COATING PROCESSES  
 427/446 SPRAY COATING UTILIZING FLAME OR PLASMA HEAT  
 (E.G., FLAME SPRAYING, ETC.)
- 2 428/210 (2 OR, 0 XR)  
 Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
 428/98 STRUCTURALLY DEFINED WEB OR SHEET (E.G.,

## OVERALL DIMENSION, ETC.)

- 428/195.1 .Discontinuous or differential coating,  
impregnation or bond (e.g., artwork, printing, retouched  
photograph, etc.)
- 428/210 ..Including ceramic, glass, porcelain or quartz  
layer
- 2 428/213 (0 OR, 2 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/98 STRUCTURALLY DEFINED WEB OR SHEET (E.G.,  
OVERALL DIMENSION, ETC.)  
428/212 .Including components having same physical  
characteristic in differing degree  
428/213 ..Thickness (relative or absolute)
- 2 428/214 (0 OR, 2 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/98 STRUCTURALLY DEFINED WEB OR SHEET (E.G.,  
OVERALL DIMENSION, ETC.)  
428/212 .Including components having same physical  
characteristic in differing degree  
428/213 ..Thickness (relative or absolute)  
428/214 ...Of adhesive layers
- 2 428/215 (1 OR, 1 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/98 STRUCTURALLY DEFINED WEB OR SHEET (E.G.,  
OVERALL DIMENSION, ETC.)  
428/212 .Including components having same physical  
characteristic in differing degree  
428/213 ..Thickness (relative or absolute)  
428/215 ...Absolute thicknesses specified
- 2 428/457 (0 OR, 2 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/411.1 COMPOSITE (NONSTRUCTURAL LAMINATE)  
428/457 .Of metal
- 2 428/462 (0 OR, 2 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/411.1 COMPOSITE (NONSTRUCTURAL LAMINATE)  
428/457 .Of metal  
428/461 ..Next to addition polymer from unsaturated  
monomers  
428/462 ...Including polyene monomers (e.g., butadiene,  
etc.)
- 2 428/623 (1 OR, 1 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/544 ALL METAL OR WITH ADJACENT METALS  
428/615 .Composite; i.e., plural, adjacent, spatially  
distinct metal components (e.g., layers, joint, etc.)  
428/621 ..with additional, spatially distinct nonmetal  
component  
428/622 ...More than one such component  
428/623 ....Adjacent to each other
- 2 428/627 (1 OR, 1 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/544 ALL METAL OR WITH ADJACENT METALS  
428/615 .Composite; i.e., plural, adjacent, spatially  
distinct metal components (e.g., layers, joint, etc.)  
428/621 ..with additional, spatially distinct nonmetal

- component  
428/627 ...Boride, carbide or nitride component
- 2 428/654 (0 OR, 2 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/544 ALL METAL OR WITH ADJACENT METALS  
428/615 .Composite; i.e., plural, adjacent, spatially  
distinct metal components (e.g., layers, joint, etc.)  
428/650 ..Al-base component  
428/654 ...Next to Al-base component
- 2 428/901 (0 OR, 2 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/901 PRINTED CIRCUIT
- 2 438/622 (1 OR, 1 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS  
438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL  
438/597 .To form ohmic contact to semiconductive  
material  
438/618 ..Contacting multiple semiconductive regions  
(i.e., interconnects)  
438/622 ...Multiple metal levels, separated by  
insulating layer (i.e., multiple level metallization)
- 2 438/675 (1 OR, 1 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS  
438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL  
438/597 .To form ohmic contact to semiconductive  
material  
438/674 ..Selective deposition of conductive layer  
438/675 ...Plug formation (i.e., in viahole)
- 2 438/699 (0 OR, 2 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS  
438/689 CHEMICAL ETCHING  
438/694 .Combined with coating step  
438/697 ..Planarization by etching and coating  
438/699 ...Plural coating steps
- 2 438/763 (0 OR, 2 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS  
438/758 COATING OF SUBSTRATE CONTAINING SEMICONDUCTOR  
REGION OR OF SEMICONDUCTOR SUBSTRATE  
438/761 .Multiple layers  
438/763 ..Layers formed of diverse composition or by  
diverse coating processes

10689792\_CLS1.txt  
Most Frequently Occurring Classifications of Patents Returned  
From A Search of 10689792 on February 21, 2006

Original Classifications

2 220/62.12  
2 428/210  
2 438/624

Cross-Reference Classifications

4 428/433  
4 438/637  
3 257/E21.162  
3 257/E21.245  
3 257/E21.266  
3 257/E21.295  
3 257/E21.58  
3 257/E23.145  
3 428/209  
3 428/461  
3 438/624  
2 117/108  
2 117/940  
2 118/308  
2 118/323  
2 118/673  
2 118/69  
2 148/33.5  
2 220/669  
2 228/122.1  
2 228/124.1  
2 257/750  
2 257/751  
2 257/758  
2 257/761  
2 257/769  
2 257/E21.585  
2 257/E21.59  
2 257/E23.106  
2 257/E23.147  
2 257/E23.167  
2 257/E29.162  
2 359/586  
2 427/422  
2 427/424  
2 428/213  
2 428/214  
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2 428/654  
2 428/901  
2 438/699  
2 438/763

Combined Classifications

5 438/624  
4 428/433  
4 428/461  
4 438/637  
3 257/758  
3 257/E21.162  
3 257/E21.245

3 257/E21.266  
3 257/E21.295  
3 257/E21.58  
3 257/E23.145  
3 428/209  
3 428/35.9  
2 117/108  
2 117/940  
2 118/308  
2 118/323  
2 118/59  
2 118/673  
2 118/69  
2 148/33.4  
2 148/33.5  
2 216/13  
2 220/62.12  
2 220/669  
2 228/121  
2 228/122.1  
2 228/124.1  
2 228/195  
2 257/750  
2 257/751  
2 257/761  
2 257/769  
2 257/E21.585  
2 257/E21.59  
2 257/E23.106  
2 257/E23.147  
2 257/E23.167  
2 257/E29.162  
2 359/586  
2 427/422  
2 427/424  
2 427/446  
2 428/210  
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2 438/675  
2 438/699  
2 438/763